

# **ABSTRACT OF THE DISCLOSURE**

A process for integrating an alignment mark and a trench device. A substrate having first and second trenches is provided. The second trench is used as the alignment  
5 mark having a width larger than the first trench. The trench device is formed in each of the low portion of the first and second trenches, and then a first conductive layer is formed on the trench device in each of the first and second trenches. A second conductive layer is formed  
10 overlying the substrate and fills in the first trench and is simultaneously and conformably formed over the inner surface of the second trench. The second conductive layer and a portion of the first conductive layer in the second trench are removed and simultaneously leave a portion of the second  
15 conductive layer in the first trench by the etch back process.